Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1460	semiconductor and polishing and polarity	USPAT	OR	OFF	2005/09/19 11:07
L2	82	semiconductor and polishing and (first adj polarity)	USPAT	OR	OFF	2005/09/19 11:07
L3	26	2 and "438"/\$.ccls.	USPAT	OR	OFF	2005/09/19 11:08
L4	47	semiconductor and polishing and (first adj polarity) and (second adj polarity)	USPAT	OR	OFF	2005/09/19 11:08
L5	. 4	4 and (polishing adj pad)	USPAT	OR	OFF	2005/09/19 11:08
L6	2	"438"/\$.ccls. and (polishing adj pad)and platen and (first adj polarity)	USPAT	OR	OFF	2005/09/19 11:08
L7	24	"438"/\$.ccls. and (polishing adj pad)and platen and polarity	USPAT	OR	OFF	2005/09/19 11:01
L8	2	"438"/\$.ccls. and (polishing adj pad)and platen and (first adj polarity)and electrodes	USPAT	OR	OFF	2005/09/19 11:06
L9	2753	semiconductor and polishing and polarity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:07
L10	76	semiconductor and polishing and (first adj polarity)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:13
L11	0	2 and "438"/\$.ccls.	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:08
L12	49	semiconductor and polishing and (first adj polarity) and (second adj polarity)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:08
L13	0	4 and (polishing adj pad)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:08
L14		"438"/\$.ccls. and (polishing adj pad)and platen and (first adj polarity)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	OFF	2005/09/19 11:08

L15	semiconductor and polishing and (first adj polarity)and ((second or opposite) adj polarity)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:14
L16	1 15 and electrode	USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:14
L17	41 15 and electrode	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:15
L18	33 · 15 and electrodes	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:16

Ref	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L9	2753	semiconductor and polishing and polarity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:07
L10	76	semiconductor and polishing and (first adj polarity)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:13
L11 .	0	2 and "438"/\$.ccls.	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:08
L12	49	semiconductor and polishing and (first adj polarity) and (second adj polarity)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:08
L13 ;	0	4 and (polishing adj pad)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:08
L14	0	"438"/\$.ccls. and (polishing adj pad)and platen and (first adj polarity)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF .	2005/09/19 11:08
L15	54	semiconductor and polishing and (first adj polarity)and ((second or opposite) adj polarity)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:14
L16	1	15 and electrode	USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:14
L17	41	15 and electrode	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:15
L18	33	15 and electrodes	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 11:16